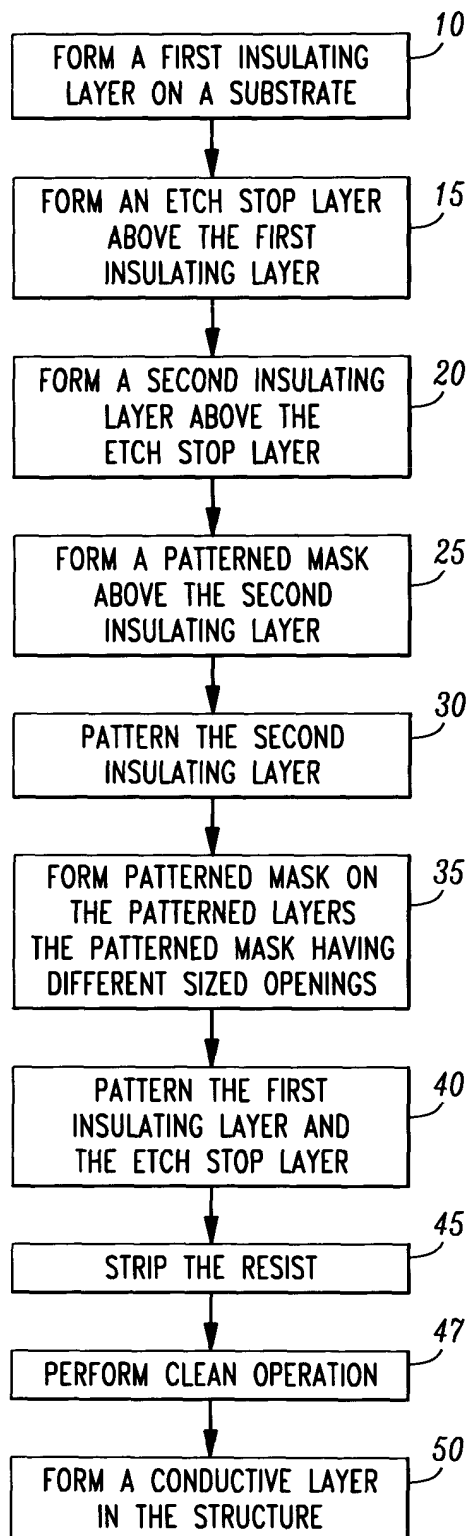
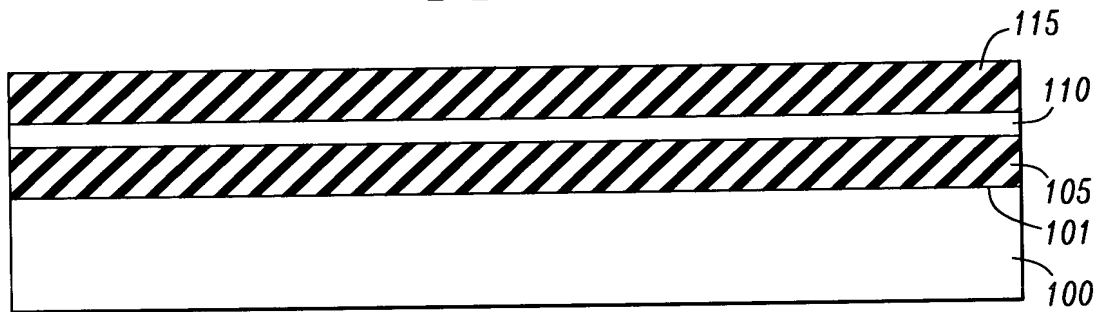


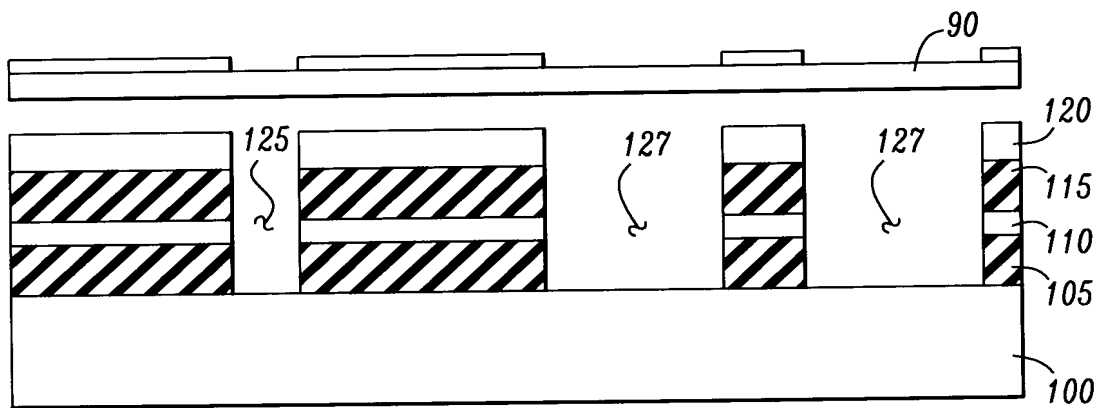
**FIG. 1**



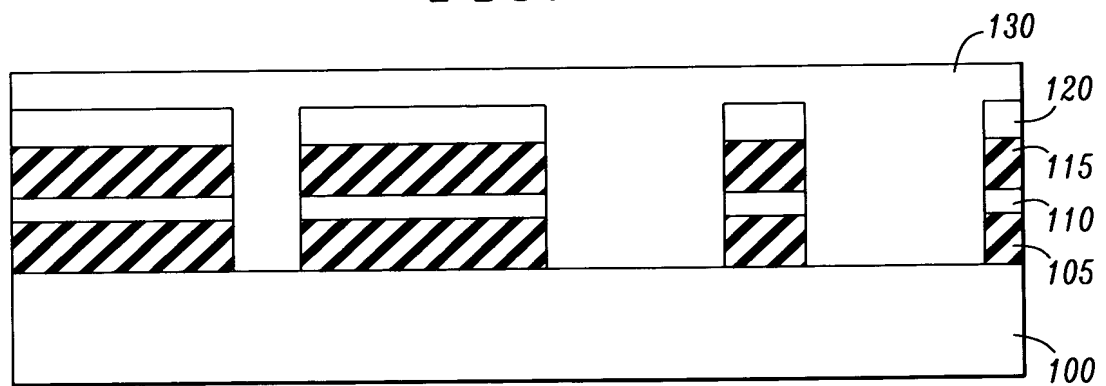
**FIG. 2**



**FIG. 3**

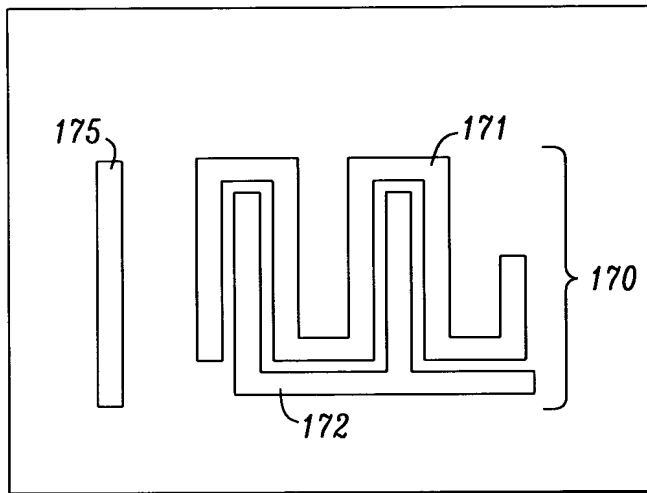
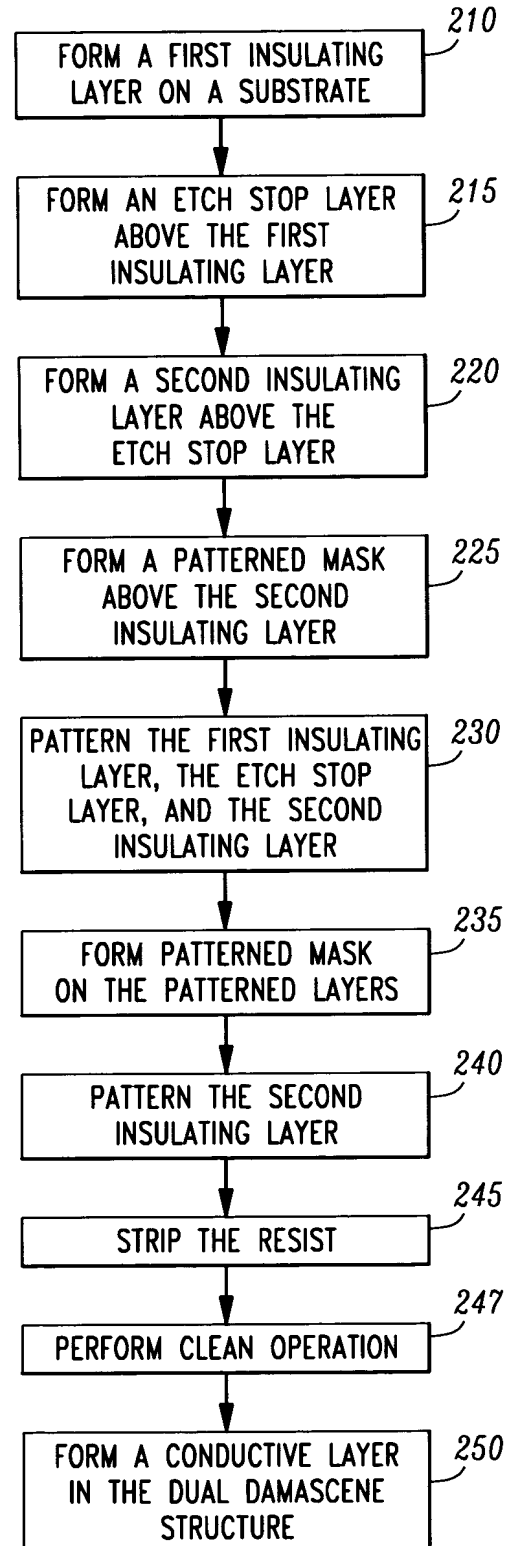


**FIG. 4**

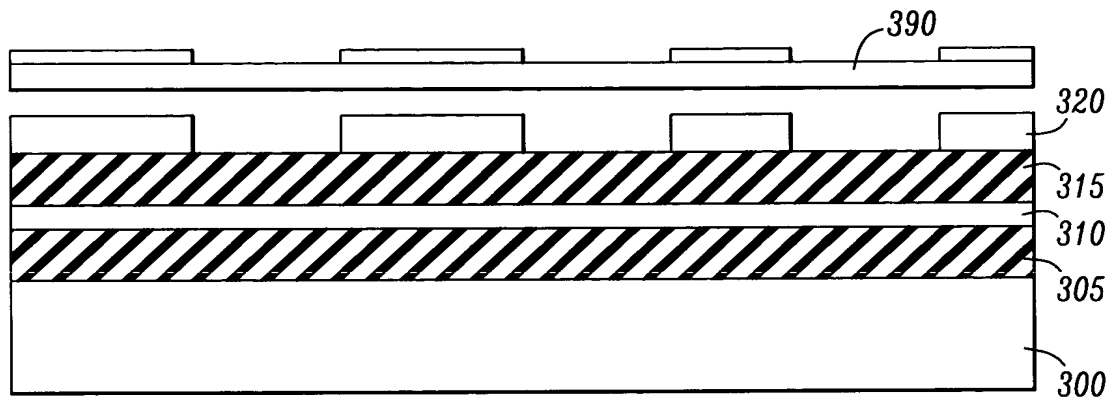


A cross-sectional view of a semiconductor device. A substrate 105 is shown at the bottom. On top of the substrate, there is a gate stack 110. The gate stack 110 consists of a gate electrode 115 and a gate dielectric layer 110. The gate electrode 115 is shown as a hatched layer, and the gate dielectric layer 110 is shown as a white layer. The gate stack 110 is positioned over a region of the substrate 105.

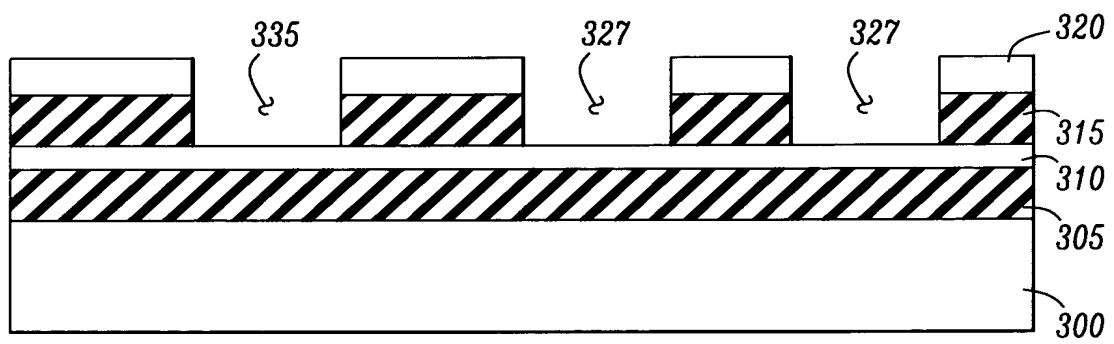
A cross-sectional view of a semiconductor device. The device consists of a substrate 105. On the substrate, there are two groups of elements. Group 175, on the left, includes a first layer 147, a second layer 145, and a third layer 147. Group 170, on the right, includes a first layer 145, a second layer 147, and a third layer 145. The top surface of the device is labeled 115, and the side surface is labeled 110.

**FIG. 8****FIG. 9**

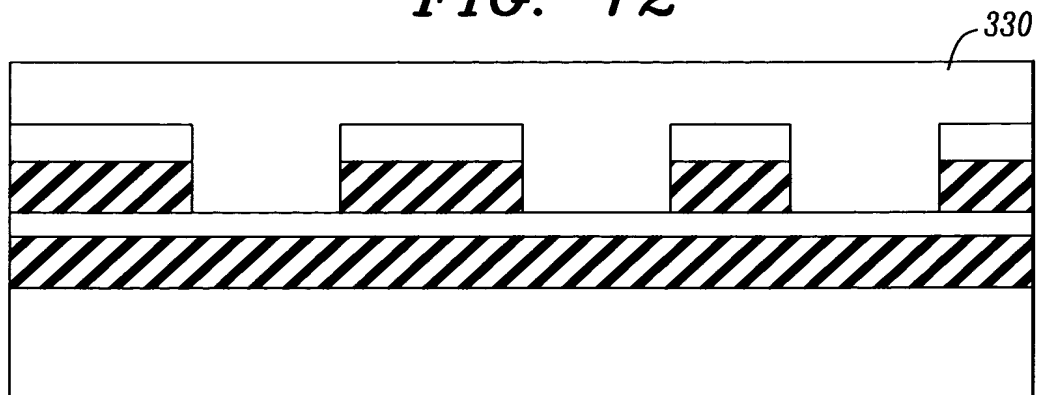
**FIG. 10**



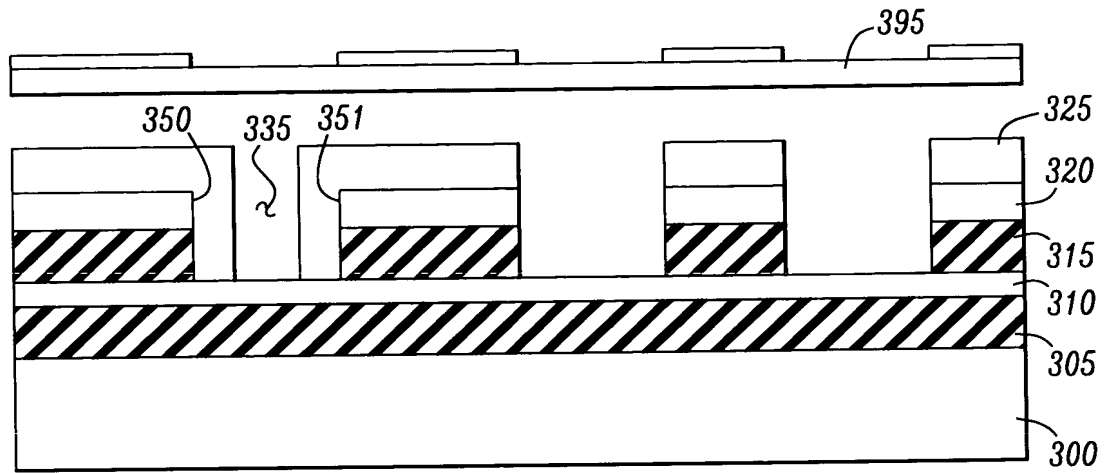
**FIG. 11**



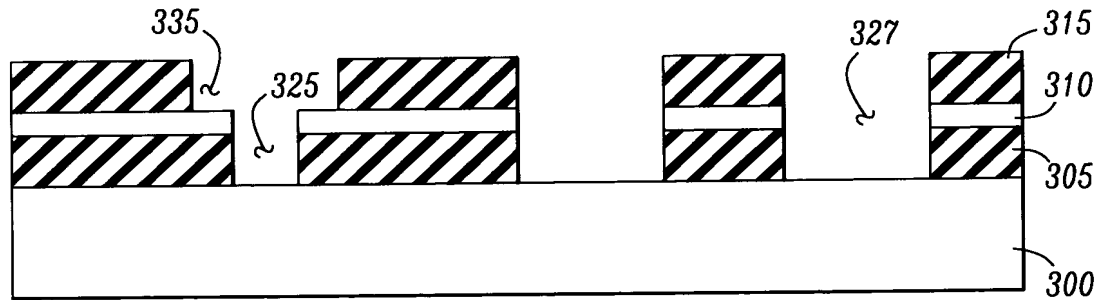
**FIG. 12**



**FIG. 13**



**FIG. 14**



**FIG. 15**

